IN THE CLAIMS:

1. (Previously Presented) A manufacturing method for an electronic device, comprising:

a hole-forming step of forming a contact hole in an insulating film that covers a conductive part formed on a first main surface of a substrate and an area surrounding the conductive part, the hole being formed beside the conductive part, and the conductive part including a first material;

a fluid-supplying step of supplying a second fluid material to the contact hole, the second fluid material having a reactive property with the first material; and

an inspection step, after the second fluid material has been supplied, of inspecting for evidence of a reaction by the conductive part with the second fluid material.

2. (Previously Presented) The manufacturing method of Claim 1, wherein

the reactive property of the second fluid material causes the conductive part to be eroded on contact with the second fluid material, and

in the inspection step, evidence that the conductive part has been eroded is inspected for.

3. (Original) The manufacturing method of Claim 2, wherein

in the inspection step, evidence of erosion is inspected for optically.

4. (Previously Presented) The manufacturing method of Claim 3, wherein

in the inspection step, evidence of erosion is inspected for after removing the second fluid material from the contact hole.

5. (Previously Presented) The manufacturing method of Claim 4, wherein

the first material is one of tungsten and a tungsten alloy, and

the second fluid material is a solution including one of hydrogen peroxide and ozone.

6. (Previously Presented) The manufacturing method of Claim 5, wherein

in the fluid-supplying step, the solution is supplied to the contact hole under a condition by which the solution is able to selectively erode the conductive part.

7. (Original) The manufacturing method of Claim 1, wherein

the electronic device is a memory device that includes a plurality of components that function as field effect transistors, and

the conductive part is a function electrode that is formed before the hole-forming step by applying a design rule that stipulates an electrode width of 0.18μm or less.

8. (Original) The manufacturing method of Claim 3, wherein

the conductive part includes a large-area portion that is sufficient in size to enable inspection thereof with an optical microscope for evidence of the reaction, and

in the inspection step, evidence of the reaction in the large-area portion is inspected for.

9. (Previously Presented) The manufacturing method of Claim 2, wherein

in the inspection step, after a material including at least the second fluid material has been removed, presence of at least one of the first material and a compound of the first material and the second fluid material is inspected for in the removed material.

10. (Previously Presented) The manufacturing method of Claim 1, wherein

the substrate has a pre-formed inspection area that is independent of other circuits areas,

in the fluid material-supplying step a contact hole formed in the inspection area is subject to the inspection, and

in the inspection step, a conductive part formed in the inspection area is subject to the inspection.

11. (Original) The manufacturing method of Claim 1, wherein

in the hole forming step, the contact hole is formed using a self-align contact method.

12. (Original) The manufacturing method of Claim 11, wherein

a silicon nitride film is provided on the substrate as an etching stopper layer in the hole forming step.

13. (Original) The manufacturing method of Claim 12, wherein

the insulating film is formed of boron phosphorus silicon glass, and

the first material has an etching selectivity ratio of 100 or higher in relation to material that composes the etching stopper layer and material that composes the insulating film.

14-17. (Cancelled).

18. (Previously Presented) An inspection method for a semiconductor member having a plurality of layers of at least two different materials formed on a substrate with portions thereof selectively removed to provide one of an electronic device and a pre-form thereof, comprising:

applying a fluid having a first characteristic property of being non-reactive to those exposed layers of the plurality of layers when one of the electronic device and the pre-form thereof is properly fabricated and a second characteristic of being reactive to one or more layers of the plurality of layers that are not exposed when properly fabricated; and

detecting a fluid reaction with one or more of materials to determine a flaw in fabrication of the one of the electronic device and the pre-form.

19. (Previously Presented) The inspection method of Claim 18 wherein the step of detecting is performed with a scanning electron microscope.

20. (Previously Presented) The inspection method of Claim 18 wherein the fluid reaction erodes away one or more of the different materials.

21. (Previously Presented) The inspection method of Claim 18 wherein the fluid reaction provides an eluted byproduct.

22. (New) The manufacturing method of Claim 1, wherein

the electronic device is a memory device that includes a plurality of components that function as field effect transistors.

23. (New) The manufacturing method of Claim 1, wherein the conductive part is a function electrode.